

KEC

KOREA ELECTRONICS CO.,LTD.

**SEMICONDUCTOR
TECHNICAL DATA****KTC3203**

EPITAXIAL PLANAR NPN TRANSISTOR

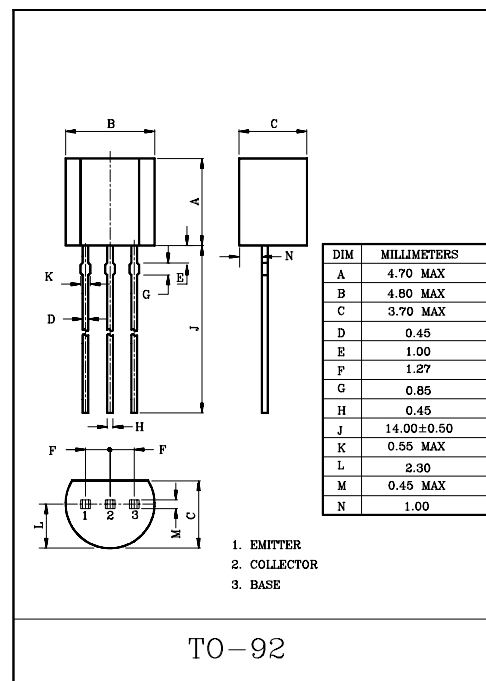
HIGH CURRENT APPLICATION.

FEATURE

- Complementary to KTA1271.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Operating Temperature	T_{opr}	-40~85	°C
Storage Temperature Range	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=35V, I_E=0$	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA$	30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=100mA$	100	-	320	
	$h_{FE(2)}$ (Note)	$V_{CE}=1V, I_C=700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1V, I_C=10mA$	0.5	-	0.8	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz, I_E=0$	-	13	-	pF

Note : $h_{FE(1)}$ Classification O:100~200, Y:160~320

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